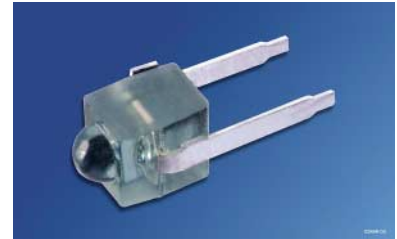


**NPN-Silizium-Fototransistor**  
**Silicon NPN Phototransistor**  
**Lead (Pb) Free Product - RoHS Compliant**

**BPX 81**



**Wesentliche Merkmale**

- Speziell geeignet für Anwendungen im Bereich von 450 nm bis 1100 nm
- Hohe Linearität
- Einstellige Zeilenbauform aus klarem Epoxy
- Gruppiert lieferbar

**Features**

- Especially suitable for applications from 450 nm to 1100 nm
- High linearity
- One-digit array package of transparent epoxy
- Available in groups

**Anwendungen**

- Computer-Blitzlichtgeräte
- Miniaturlichtschranken für Gleich- und Wechsellichtbetrieb
- Industrieelektronik
- „Messen/Steuern/Regeln“

**Applications**

- Computer-controlled flashes
- Miniature photointerrupters
- Industrial electronics
- For control and drive circuits

Typ Type	Bestellnummer Ordering Code	Fotostrom , $E_e = 0.5 \text{ mW/cm}^2$ , $\lambda = 950 \text{ nm}$ , $V_{CE} = 5 \text{ V}$ Photocurrent $I_{PCE} \text{ (mA)}$
BPX 81	Q62702P0020	> 0.25
BPX 81-2/3	Q62702P3583	0.25..0.80
BPX 81-3	Q62702P0043S0003	0.40..0.80
BPX 81-3/4	Q62702P3584	> 0.40
BPX 81-4	Q62702P0043S0004	> 0.63

**Grenzwerte**  
**Maximum Ratings**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ...+ 80	°C
Kollektor-Emitterspannung Collector-emitter voltage	$V_{CE}$	35	V
Kollektorstrom Collector current	$I_C$	50	mA
Kollektorspitzenstrom, $\tau < 10 \mu s$ Collector surge current	$I_{CS}$	200	mA
Verlustleistung, $T_A = 25 \text{ }^\circ\text{C}$ Total power dissipation	$P_{tot}$	90	mW
Wärmewiderstand Thermal resistance	$R_{thJA}$	750	K/W

**Kennwerte** ( $T_A = 25\text{ °C}$ ,  $\lambda = 950\text{ nm}$ )

**Characteristics**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S_{\max}}$	850	nm
Spektraler Bereich der Fotoempfindlichkeit $S = 10\%$ von $S_{\max}$ Spectral range of sensitivity $S = 10\%$ of $S_{\max}$	$\lambda$	450 ...1100	nm
Bestrahlungsempfindliche Fläche Radiant sensitive area	$A$	0.11	mm <sup>2</sup>
Abmessung der Chipfläche Dimensions of chip area	$L \times B$ $L \times W$	$0.5 \times 0.5$	mm $\times$ mm
Halbwinkel Half angle	$\varphi$	$\pm 18$	Grad deg.
Kapazität Capacitance $V_{CE} = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$	$C_{CE}$	7.5	pF
Dunkelstrom Dark current $V_{CE} = 20\text{ V}$ , $E = 0$	$I_{CEO}$	1 ( $\leq 50$ )	nA

Die Fototransistoren werden nach ihrer Fotoempfindlichkeit gruppiert und mit arabischen Ziffern gekennzeichnet.

The phototransistors are grouped according to their spectral sensitivity and distinguished by arabian figures.

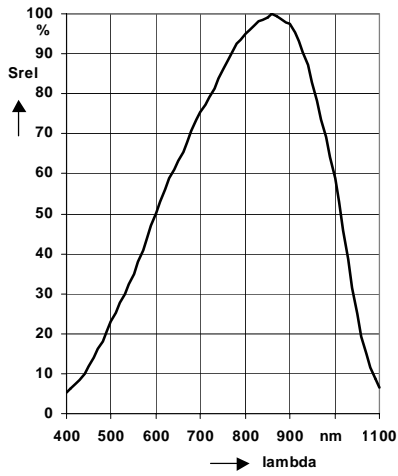
Bezeichnung Parameter	Symbol Symbol	Wert Value			Einheit Unit
		-2	-3	-4	
Fotostrom, $\lambda = 950 \text{ nm}$ Photocurrent $E_e = 0.5 \text{ mW/cm}^2$ , $V_{CE} = 5 \text{ V}$ $E_v = 1000 \text{ lx}$ , Normlicht/standard light A, $V_{CE} = 5 \text{ V}$	$I_{PCE}$ $I_{PCE}$	0.25..0.50 1.2	0.40..0.80 1.9	$\geq 0.63$ 2.9	mA mA
Anstiegszeit/Abfallzeit Rise and fall time $I_C = 1 \text{ mA}$ , $V_{CC} = 5 \text{ V}$ , $R_L = 1 \text{ k}\Omega$	$t_r$ , $t_f$	5.5	6	8	$\mu\text{s}$
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage $I_C = I_{PCEmin}^{1)} \times 0.3$ $E_e = 0.5 \text{ mW/cm}^2$	$V_{CEsat}$	150	150	150	mV

1)  $I_{PCEmin}$  ist der minimale Fotostrom der jeweiligen Gruppe.

1)  $I_{PCEmin}$  is the min. photocurrent of the specified group.

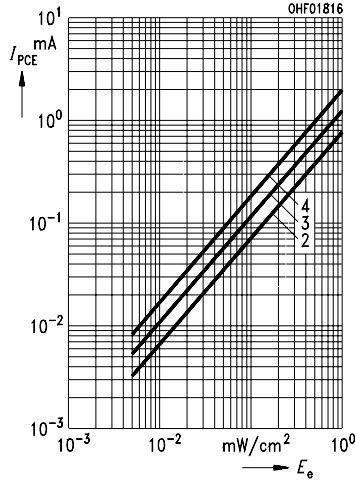
**Relative Spectral Sensitivity**

$S_{rel} = f(\lambda)$



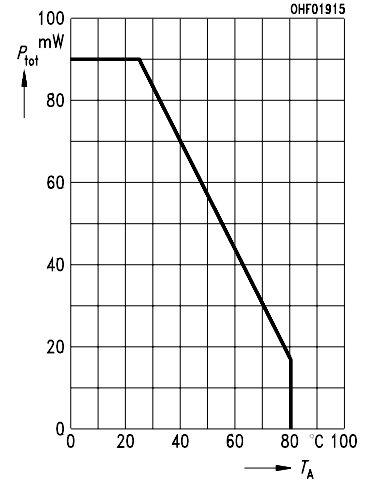
**Photocurrent**

$I_{PCE} = f(E_e), V_{CE} = 5 V$



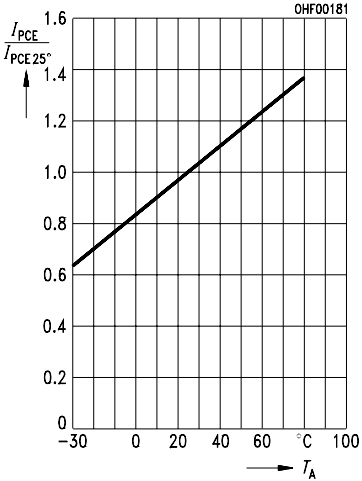
**Total Power Dissipation**

$P_{tot} = f(T_A)$



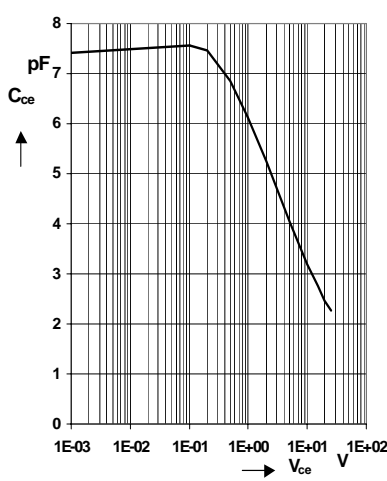
**Photocurrent**

$I_{PCE}/I_{PCE25^\circ} = f(T_A), V_{CE} = 5 V$



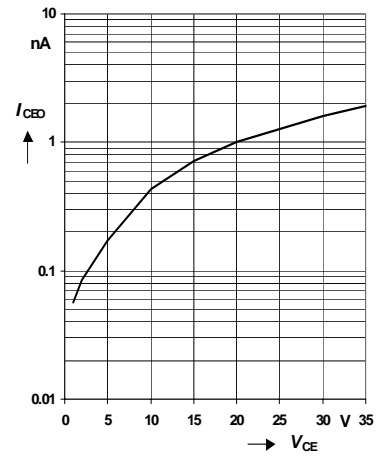
**Collector-Emitter Capacitance**

$C_{CE} = f(V_{CE}), f = 1 MHz, E = 0$



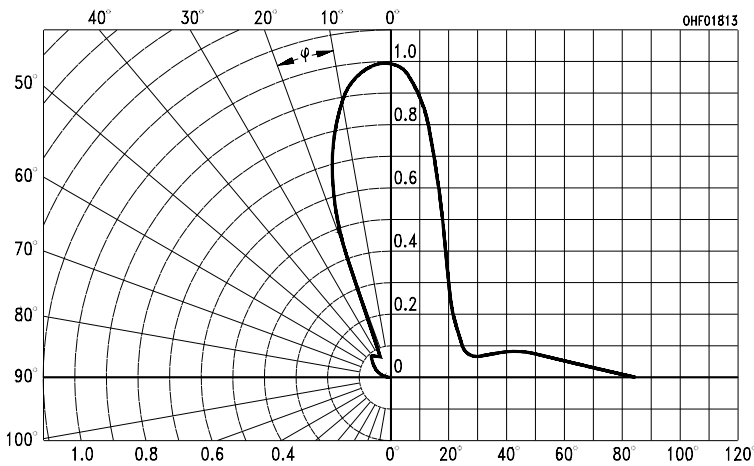
**Dark Current**

$I_{CEO} = f(V_{CE}), E = 0$



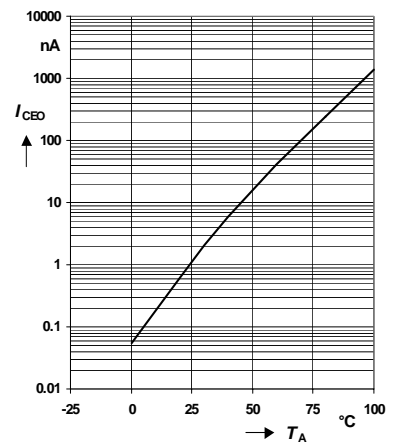
**Directional Characteristics**

$S_{rel} = f(\varphi)$

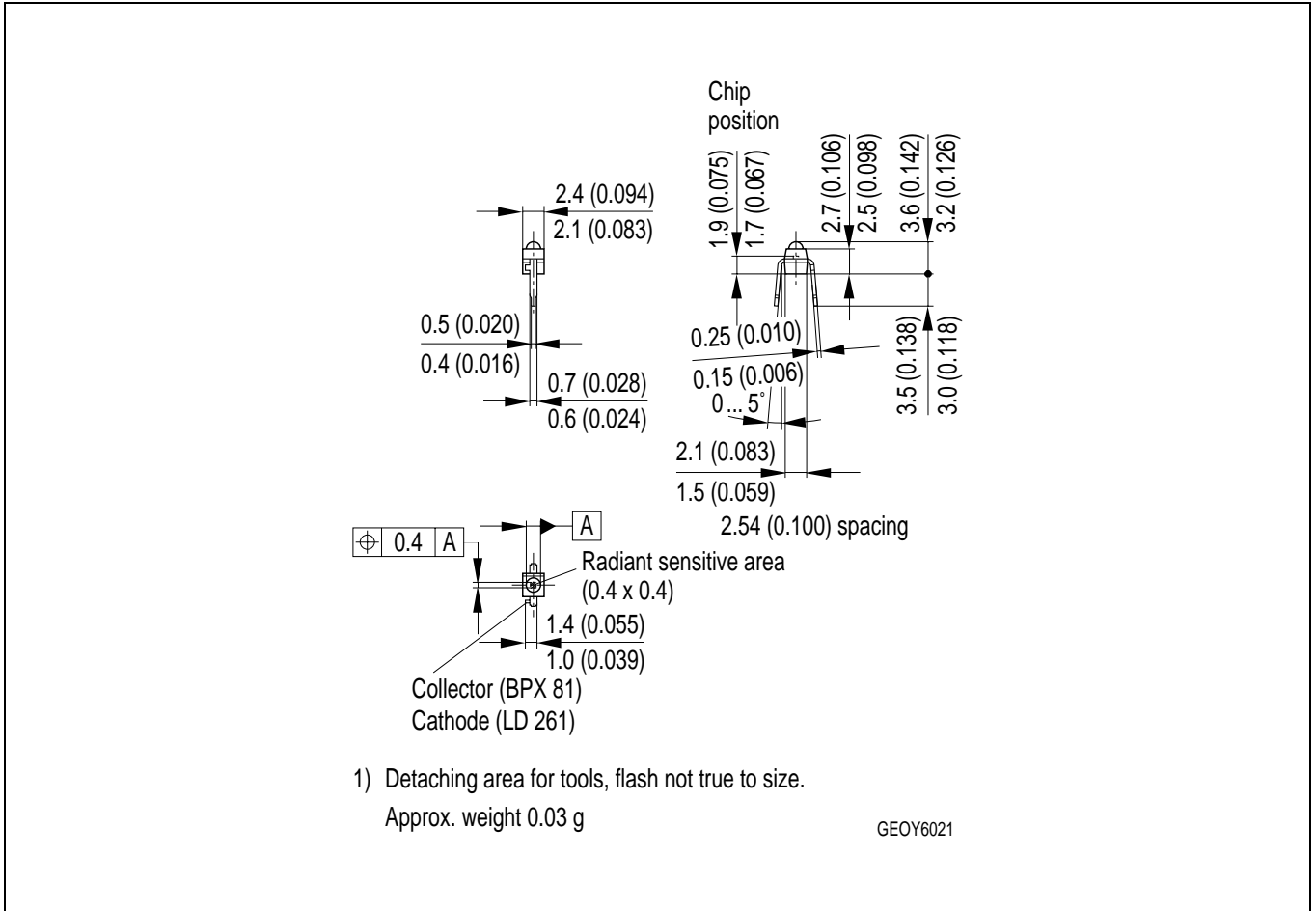


**Dark Current**

$I_{CEO} = f(T_A), V_{CE} = 20 V, E = 0$



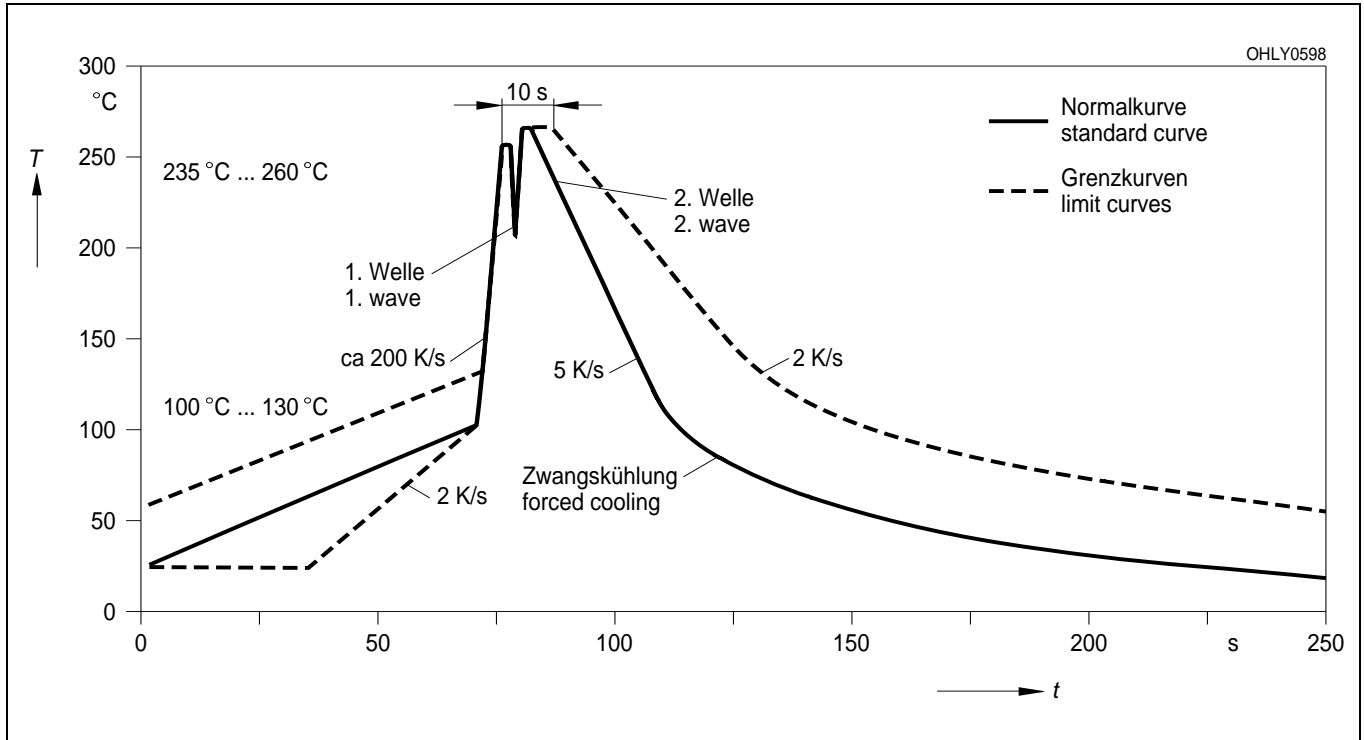
Maßzeichnung  
Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

**Lötbedingungen**  
**Soldering Conditions**  
**Wellenlöten (TTW)**  
**TTW Soldering**

(nach CECC 00802)  
(acc. to CECC 00802)



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<sup>2</sup> Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered.